

REMARKS

Claims 1-7 and 9-16 are pending in the application, with claims 9-16 having been withdrawn from consideration..

Claims 1 and 4 have been amended to correct minor typographical errors which were made in the Amendment which was filed on February 24, 2003. No new matter has been added.

Conclusion

In view of the aforementioned amendments and accompanying remarks, all of the pending claims are in condition for allowance, which action, at an early date, is requested.

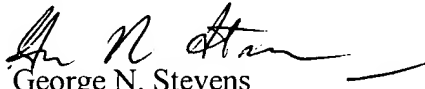
If, for any reason, it is felt that this application is not now in condition for allowance, the Examiner is requested to contact Applicants undersigned attorney at the telephone number indicated below to arrange for an interview to expedite the disposition of this case.

Attached hereto is a marked-up version of the changes made to the claims by the current amendment. The attached page is captioned "Version with markings to show changes made."

In the event that this paper is not timely filed, Applicants respectfully petition for an appropriate extension of time. Please charge any fees for such an extension of time and any other fees which may be due with respect to this paper, to Deposit Account No. 01-2340.

Respectfully submitted,

ARMSTRONG, WESTERMAN & HATTORI, LLP


George N. Stevens
Attorney for Applicant
Reg. No. 36,938

GNS/alw

Atty. Docket No. 001241
Suite 1000, 1725 K Street, N.W.

Washington, D.C. 20006

(202) 659-2930



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PATENT TRADEMARK OFFICE

Enclosures: Version with markings to show changes made

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VERSION WITH MARKINGS TO SHOW CHANGES MADE 09/669,448

IN THE CLAIMS:

Please amend claims 1 and 4 as follows:

1. (Twice Amended) A semiconductor laser device comprising:

a substrate;

a first conductivity type cladding layer;

an emission layer;

a second conductivity type cladding layer containing Al as a group III element and formed with a ridge portion;

a current blocking layer, formed on said second conductivity type cladding layer around said ridge portion, containing Al as a group III element in this order, wherein

an angle θ of inclination on a side surface of said ridge portion with respect to an upper surface of said substrate is at least 70° and not more than 117° ,

a distance t between said emission layer and said current blocking layer satisfies a relation of $[t \geq 0.275/(1 - (X2-X1))] \quad t \leq 0.275/(1 - (X2-X1))$ micrometer assuming that $X1$ represents a composition ratio of Al in group III elements forming said second conductivity type cladding layer, $X2$ represents a composition ratio of Al in group III elements forming said current blocking layer, and

a lower width W of said ridge portion is at least $2 \mu\text{m}$ and not more than $5 \mu\text{m}$.

4. **(Twice Amended)** The semiconductor laser device according to claim 1, wherein
said distance t between said emission layer and said current blocking layer satisfies a relation
of $[t \in 0.252/(1 - (X2-X1))]$ $t \leq 0.252/(1 - (X2-X1))$ micrometer.